NPN Epitaxial Planar Silicon Transistor



2SC4204

High-hFE, AF Amplifier Applications

Applications

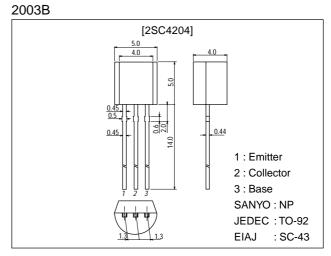
· AF amplifier, various drivers.

Features

- · Adoption of MBIT process.
- High DC current gain (h_{FE} =800 to 3200).
- · Large current capacity ($I_C=0.7A$).
- · Low collector-to-emitter saturation voltage $(V_{CE(sat)} \le 0.5V)$.
- High V_{EBO} ($V_{EBO} \ge 15V$).

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		30	V
Collector-to-Emitter Voltage	VCEO		25	V
Emitter-to-Base Voltage	V _{EBO}		15	V
Collector Current	ι _C		0.7	A
Collector Current (Pulse)	I _{CP}		1.5	A
Collector Dissipation	PC		0.6	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

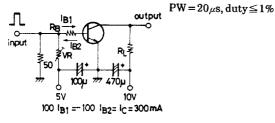
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0			0.1	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =50mA	800	1500	3200	
	h _{FE} 2	$V_{CE}=5V, I_{C}=500$ mA	600			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA		270		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		9		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =10mA		0.15	0.50	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =500mA, I _B =10mA		0.9	1.2	V

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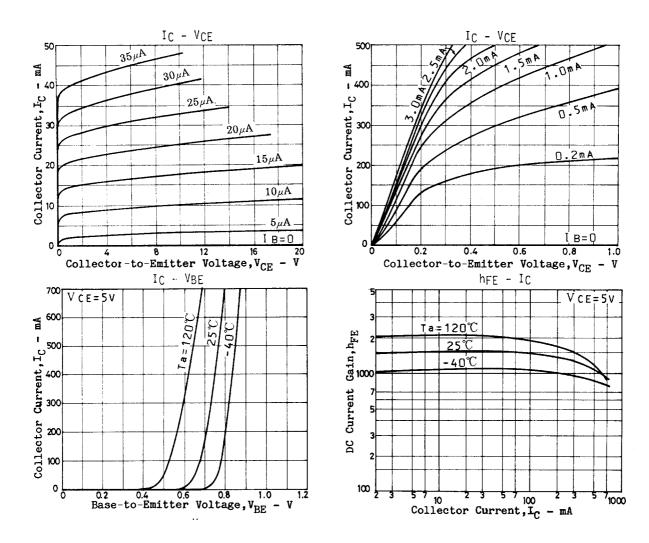
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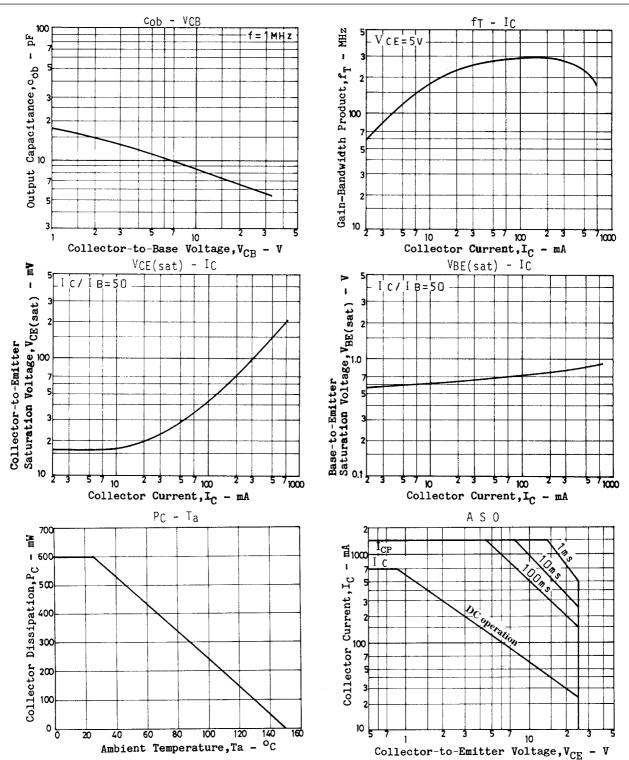
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10µA, I _E =0	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	25			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	15			V
Turn-ON Time	ton	See specified test circuit.		0.1		μs
Storage Time	^t stg	See specified test circuit.		0.6		μs
Fall Time	t _f	See specified test circuit.		0.06		μs

Switching Time Test Circuit



Unit (resistance : Ω , capacitance : F)





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